

## **Quarterly Reliability Monitoring Results**

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier		User Part Number						
Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		BC847DS Part Description						
								Nexperia DHAM Small Signal Bipolar Transistor
		SMD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
			TEST					
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	849	61170	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
		Tj = Tjmax, Vr = 100% of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	202	16160	0		
	тс	JESD22-A104						
# A4	Temperature Cycling	-65 °C to Timax, not to exceed 150°C	1000 cycles	171	13680	0		
	remperature cycling		1000 Cycles	1/1	13080	0		
	AC	JESD22-A102						
# AD - H	Autoclave	Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia)		170	12040	0		
# A3 alt	Autoclave	Plessure = 203  kPa (29.7  psia)	96 hours	173	13840	0		
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias		1000 hours	173	13840	0		
# AZ alt	Temperature Reverse blas		1000 nours	175	13840	0		
	IOL	MIL-STD-750 Method 1037						
# AF	Intermittent Operating Life	ton = toff, devices powered to insure $\Delta T_j$ =	1000 have	107	15360	0		
# A5	Internitient Operating Life		1000 hours	197	15760	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	$260 \circ C \pm 5 \circ C$	10 s	135	4050	0		
+ 0	SD	200 010 0	10.5	100	4030	U		
# C10	Solderability	J-STD-002		242	2420	0		
# C10	Solder ability	J-31D-002		342	3420	0		

[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia DHAM	Small Signal Bipolar Transistor	16160	0	0.26	3.81E+09

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